ABSTRACT

A process for manufacturing a hollow silicon structure is simplified. A device for manufacturing the silicon structure is a device that manufactures the hollow silicon structure by processing a silicon structure, the silicon structure consisting of a silicon oxide layer formed on a silicon substrate, the silicon oxide layer being covered by a silicon layer. The device is provided with first gas supply members 20 and 21, second gas supply members 30 and 31, an etching reaction chamber 10, selective connecting means 23 to 26, 34 and 35, and a gas discharging means 42. The first gas etches silicon. The second gas etches silicon oxide and barely etches silicon. The selective connecting means 23 to 26, 34 and 35 selectively connect the etching reaction chamber 10 with either the first gas supply members 20 and 21 or the second gas supply members 30 and 31. The gas discharging means 42 discharges gas from the etching reaction chamber 10.



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